

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|--------------------------------|--|----------------------|----------|
| 1 | BRS | L1 | 229 | sakaguchi near kiyofumi.in. | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:47 | |
| 2 | BRS | L2 | 0 | 438/305.\$ccls. | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:47 | |
| 3 | BRS | L3 | 2065 | 438/305.cccls. | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:48 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|-------|--|--|----------------------|----------|
| 4 | BRS | L4 | 0 | 3 and (separation near layer) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:48 | |
| 5 | BRS | L5 | 41 | 3 and (separation) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:49 | |
| 6 | BRS | L6 | 24468 | (separation) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:49 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|--|--|----------------------|----------|
| 7 | BRS | L7 | 1323 | (separation near layer) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:50 | |
| 8 | BRS | L8 | 133 | (separation near layer) near25 (second near substrate) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:50 | |
| 9 | BRS | L9 | 7 | (separation near layer) near25 (second near substrate) near25 (implant\$3) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 19:53 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|---|--|------------------|----------|
| 10 | BRS | L10 | 959 | (second near substrate) near25 (implant\$3) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/12 19:54 | |
| 11 | BRS | L11 | 210 | (second near substrate) near25 (first near substrate) near25 (implant\$3) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/12 20:15 | |
| 12 | BRS | L12 | 959 | (second near substrate) near25 (implant\$3) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/12 20:16 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|---|--|----------------------|----------|
| 13 | BRS | L13 | 50 | (second near substrate) near25 (implant\$3) near35 (semiconductor near layer) | USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB | 2004/10/1 2 20:16 | |

| | U | 1 | Document ID | Title | Current OR | Pages |
|---|-------------------------------------|--------------------------|-------------------------|--|------------|-------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US A1 20040048454 | Substrate and manufacturing method therefor | 438/486 | 27 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US A1 20030170990 | PROCESS FOR MANUFACTURING A SEMICONDUCTOR SUBSTRATE AS WELL AS A SEMICONDUCTOR THIN FILM, AND MULTILAYER STRUCTURE | 438/690 | 42 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US A1 20030038383 | Semiconductor substrate and process for its production | 257/797 | 32 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US A1 20010038153 | Semiconductor substrate and process for its production | 257/797 | 32 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US B1 6700631 | Method of separating thin-film device, method of transferring thin-film device, thin-film device, active matrix substrate, and liquid crystal display device | 349/45 | 35 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US B1 6613678 | Process for manufacturing a semiconductor substrate as well as a semiconductor thin film, and multilayer structure | 438/695 | 42 |
| 7 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | EP A2 961312 | SOI Substrate formed by bonding | | 47 |